

HVGT High voltage silicon rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### SHAPE DISPLAY:



### FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

### APPLICATIONS:

1. Ignition device power supply.
2. Microwave emission power.
3. General purpose high voltage rectifier.

### MECHANICAL DATA:

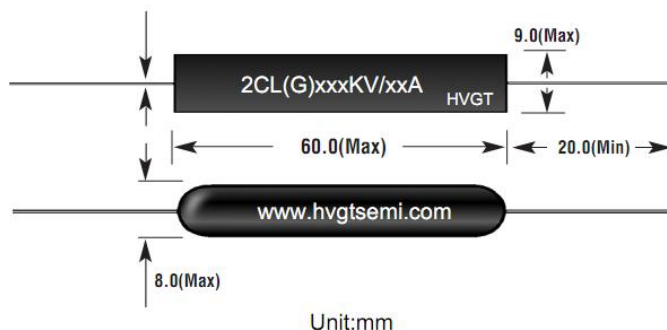
1. Case: epoxy resin molding.
2. Terminal: external lead.
3. Net weight: 7.0 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: HVS-080960H

### HVS-080960H Series

Lead Diameter 1.0mm



Unit:mm

### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renserse Voltage	$V_{RRM}$	$T_a=25^{\circ}C$ ;	40	kV
Average Output Current	$I_F$	$T_a=25^{\circ}C$ ;Resistive Load	100	mA
Suege Current	$I_{FSM}$	$T_a=25^{\circ}C$ ;8.3 mS	3.0	A
Junction Temperature	$T_J$		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	$T_c$		125	$^{\circ}C$
Storage Temperature	$T_{STG}$		-40~+125	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	$V_F$	at $25^{\circ}C$ ; $I_F=I_{F(AV)}$	48	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ ; $V_R=V_{RRM}$	5.0	$\mu A$
	$I_{R2}$	at $100^{\circ}C$ ; $V_R=V_{RRM}$	50	$\mu A$
Maximum Reverse Recovery Time	$T_{RR}$	at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	$C_J$	at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$	--	pF